

November 2013

### FDI030N06

# N-Channel PowerTrench<sup>®</sup> MOSFET 60 V, 193 A, 3.2 m $\Omega$

#### **Features**

- $R_{DS(on)}$  = 2.6 m $\Omega$  (Typ.) @  $V_{GS}$  = 10 V,  $I_D$  = 75 A
- · Fast Switching Speed
- · Low Gate Charge
- High Performance Trench Technology for Extremely Low  $R_{DS(\text{on})}$
- · High Power and Current Handling Capability
- · RoHS Compliant

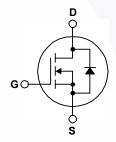
#### **Description**

This N-Channel MOSFET is produced using Fairchild Semiconductor's advanced PowerTrench® process that has been tailored to minimize the on-state resistance while maintaining superior switching performance.

#### **Applications**

- · Synchronous Rectification for ATX / Server / Telecom PSU
- · Battery Protection Circuit
- · Motor Drives and Uninterruptible Power Supplies
- · Renewable System





#### **MOSFET Maximum Ratings** T<sub>C</sub> = 25°C unless otherwise note.

Symbol		Parameter	FDI030N06	Unit
V <sub>DSS</sub>	Drain to Source Voltage	60	V	
V <sub>GSS</sub>	Gate to Source Voltage	±20	V	
		- Continuous (T <sub>C</sub> = 25°C, Silicon Limit	ed) 193*	
D	Drain Current	- Continuous (T <sub>C</sub> = 100°C, Silicon Lim	ited) 136*	Α
		- Continuous (T <sub>C</sub> = 25°C, Package Lin	nited) 120	
DM	Drain Current	- Pulsed (No	ote 1) 772	Α
E <sub>AS</sub>	Single Pulsed Avalanche Energy (Note 2)		ote 2) 1434	mJ
dv/dt	Peak Diode Recovery dv/dt (Note 3)		ote 3) 6	V/ns
n	Dawar Dissipation	(T <sub>C</sub> = 25°C)	231	W
P <sub>D</sub> Power Dissipation		- Derate Above 25°C	1.54	W/°C
T <sub>J</sub> , T <sub>STG</sub>	Operating and Storage Te	mperature Range	-55 to +175	°C
T <sub>L</sub>	Maximum Lead Temperat 1/8" from Case for 5 Seco	300	°С	

<sup>\*</sup>Calculated continuous current based on maximum allowable junction temperature. Package limitation current is 120A.

#### **Thermal Characteristics**

Symbol	Parameter	FDI030N06	Unit
$R_{\theta JC}$	Thermal Resistance, Junction to Case, Max.	0.65	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient, Max.	62.5	-C/VV

### **Package Marking and Ordering Information**

Part Number	Top Mark	Package	Packing Method	Reel Size	Tape Width	Quantity
FDI030N06	FDI030N06	I <sup>2</sup> -PAK	Tube	N/A	N/A	50 units

#### **Electrical Characteristics** $T_C = 25^{\circ}C$ unless otherwise noted.

Symbol	Parameter	Test Conditions	Min.	Тур.	Max.	Unit
Off Charac	cteristics					
BV <sub>DSS</sub>	Drain to Source Breakdown Voltage	$I_D = 250 \mu A, V_{GS} = 0 V, T_C = 25^{\circ} C$	60	-	-	V
ΔBV <sub>DSS</sub> / ΔT <sub>J</sub>	Breakdown Voltage Temperature Coefficient	I <sub>D</sub> = 1 mA, Referenced to 25°C	-	0.05	-	V/°C
I	Zero Gate Voltage Drain Current	$V_{DS} = 48 \text{ V}, V_{GS} = 0 \text{ V}$	-	-	1	μА
IDSS	Zero Gate Voltage Brain Gurrent	$V_{DS} = 48 \text{ V}, T_{C} = 150^{\circ}\text{C}$	-	-	500	μΛ
$I_{GSS}$	Gate to Body Leakage Current	$V_{GS} = \pm 20 \text{ V}, V_{DS} = 0 \text{ V}$	-	-	±100	nA

#### **On Characteristics**

V <sub>GS(th)</sub>	Gate Threshold Voltage	$V_{GS} = V_{DS}, I_{D} = 250 \mu\text{A}$	2.5	3.5	4.5	V
R <sub>DS(on)</sub>	Static Drain to Source On Resistance	V <sub>GS</sub> = 10 V, I <sub>D</sub> = 75 A	-	2.6	3.2	mΩ
9 <sub>FS</sub>	Forward Transconductance	V <sub>DS</sub> = 10 V, I <sub>D</sub> = 75 A	-	154	-	S

#### **Dynamic Characteristics**

C <sub>iss</sub>	Input Capacitance	V 05.V.V 0.V	-	7380	9815	pF
Coss	Output Capacitance	$V_{DS} = 25 \text{ V}, V_{GS} = 0 \text{ V},$ f = 1 MHz	-	1095	1455	pF
C <sub>rss</sub>	Reverse Transfer Capacitance	1 = 1 WHZ	-	415	625	pF
Q <sub>g(tot)</sub>	Total Gate Charge at 10V	V <sub>DS</sub> = 48 V, I <sub>D</sub> = 75 A,	-	116	151	nC
$Q_{gs}$	Gate to Source Gate Charge	V <sub>GS</sub> = 10 V	-	40	-	nC
$Q_{gd}$	Gate to Drain "Miller" Charge	(Note	4) _	35	-	nC

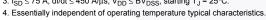
#### **Switching Characteristics**

t <sub>d(on)</sub>	Turn-On Delay Time		-	39	87	ns
t <sub>r</sub>	Turn-On Rise Time	$V_{DD} = 30 \text{ V}, I_{D} = 75 \text{ A},$	-	178	366	ns
t <sub>d(off)</sub>	Turn-Off Delay Time	$V_{GS}$ = 10 V, $R_G$ = 4.7 $\Omega$	-	54	118	ns
t <sub>f</sub>	Turn-Off Fall Time	(Note 4)	-	33	76	ns

#### **Drain-Source Diode Characteristics**

I <sub>S</sub>	Maximum Continuous Drain to Source Diode Forward Current	-/-	-	193	Α
I <sub>SM</sub>	Maximum Pulsed Drain to Source Diode Forward Current	-	-	772	Α
$V_{SD}$	Drain to Source Diode Forward Voltage V <sub>GS</sub> = 0 V, I <sub>SD</sub> = 75 A		-	1.3	V
t <sub>rr</sub>	Reverse Recovery Time $V_{GS} = 0 \text{ V}, I_{SD} = 75 \text{ A},$	-	46	-	ns
Q <sub>rr</sub>	Reverse Recovery Charge dI <sub>F</sub> /dt = 100 A/μs		50	-	nC

- 1. Repetitive rating: pulse-width limited by maximum junction temperature.
- 2. L = 0.51 mH, I  $_{AS}$  = 75 A, V  $_{DD}$  = 50 V, R  $_{G}$  = 25  $\!\Omega$  , starting T  $_{J}$  = 25  $\!^{\circ}$  C.
- 3. I  $_{SD}$   $\leq$  75 A, di/dt  $\leq$  450 A/µs, V  $_{DD}$   $\leq$  BV  $_{DSS}$  , starting T  $_{J}$  = 25°C.



#### **Typical Performance Characteristics**

Figure 1. On-Region Characteristics

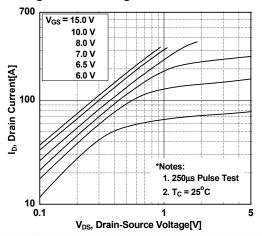


Figure 3. On-Resistance Variation vs.
Drain Current and Gate Voltage

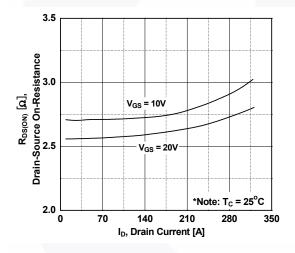


Figure 5. Capacitance Characteristics

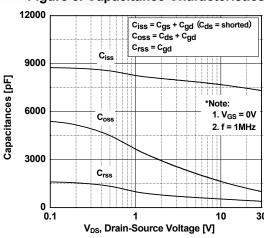


Figure 2. Transfer Characteristics

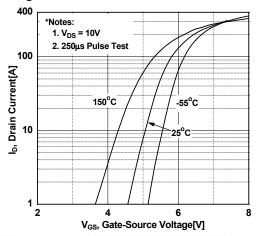


Figure 4. Body Diode Forward Voltage Variation vs. Source Current and Temperature

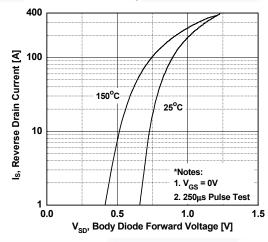
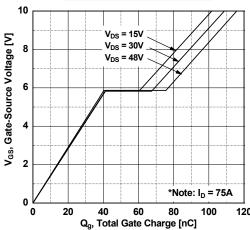


Figure 6. Gate Charge Characteristics



### **Typical Performance Characteristics** (Continued)

Figure 7. Breakdown Voltage Variation vs. Temperature

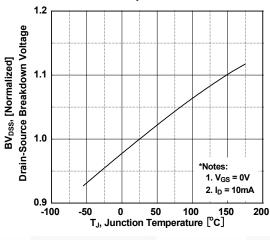


Figure 8. On-Resistance Variation vs. Temperature

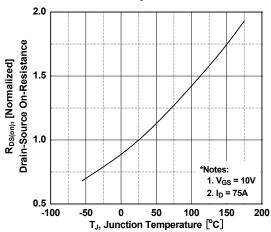


Figure 9. Maximum Safe Operating Area

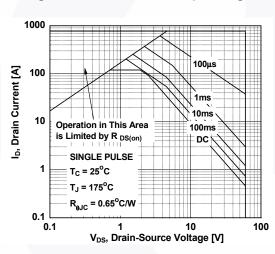


Figure 10. Maximum Drain Current vs. Case Temperature

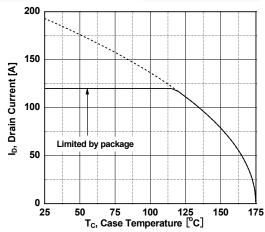
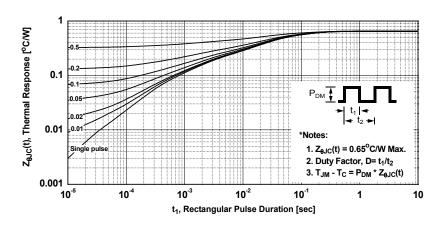


Figure 11. Transient Thermal Response Curve



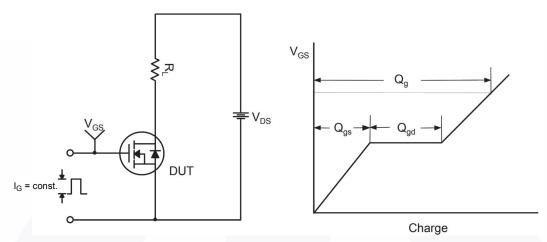


Figure 12. Gate Charge Test Circuit & Waveform

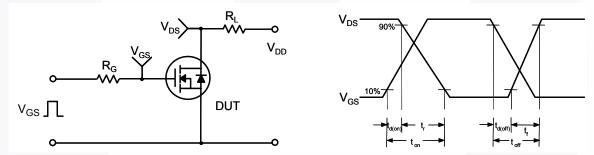


Figure 13. Resistive Switching Test Circuit & Waveforms

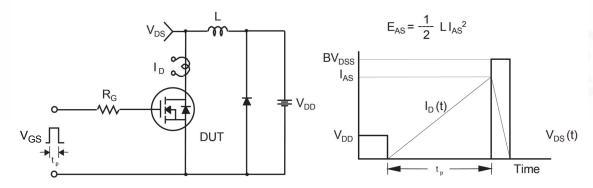


Figure 14. Unclamped Inductive Switching Test Circuit & Waveforms

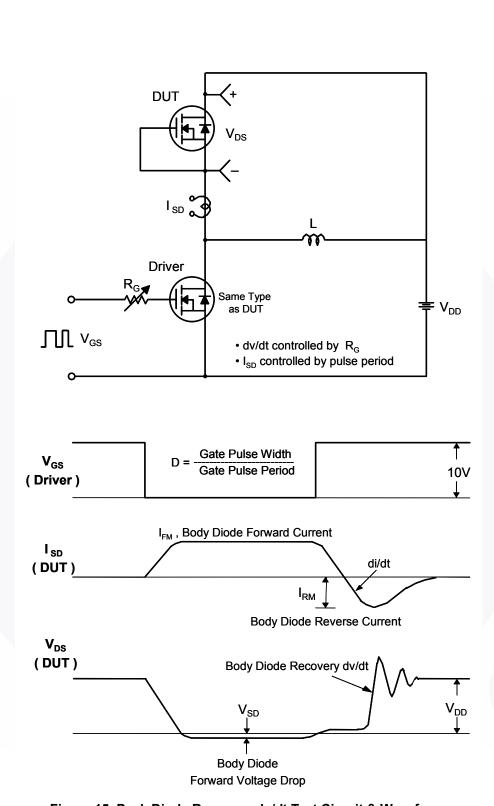


Figure 15. Peak Diode Recovery dv/dt Test Circuit & Waveforms

#### **Mechanical Dimensions**

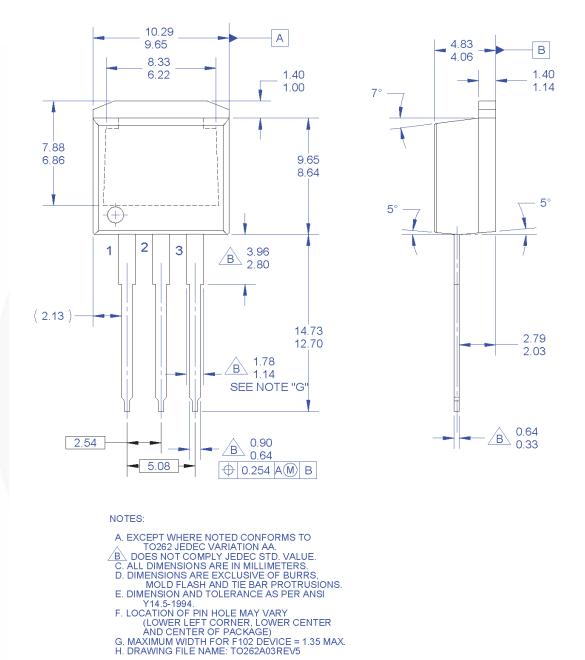


Figure 16. TO262 (I<sup>2</sup>PAK), Molded, 3-Lead, Jedec Variation AA

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